

Thermal resistance, junction-to-ambient	$R_{\theta JA}$	25	80	°C/W
Thermal resistance, junction-to-case	$R_{\theta JC}$	5	4.3	°C/W
<b>Parameter</b>	<b>Symbol</b>	<b>MMX00BJK22</b>	<b>MMG00BJK22</b>	<b>Unit</b>

## Thermal Characteristics

Diode pulse current <sub>(5)</sub>	$I_{S}^{pulse}$	12		A
Continuous diode forward current <sub>(1)</sub>	$I_{S}$	2		A
Operating and storage temperature range	$T_{stg}, T_{op}$	-25 to +120		°C
- Derate above 52°C		2.0	0.53	mW/°C
Power dissipation ( $T_C = 52°C$ )	$P_D$	25	25	W
Avalanche current, repetitive <sub>(5)</sub>	$I_{AV}$	3.1		A
Avalanche energy, repetitive <sub>(5)</sub>	$E_{AV}$	1.0		µJ
Avalanche energy, single pulse <sub>(3)</sub>	$E_{AS}$	25		µJ
Gate-source voltage	$V_{GS}$	±30		V